Silicon Epitaxial Planar Transistor NPN, 40V, 200mA



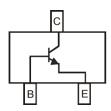


Features:

Power dissipation.(P_C=0.2W)

Applications:

· Audio frequency general purpose amplifier



Maximum Rating: @ TA = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	60		
Collector-Emitter Voltage	V _{CEO}	40	V	
Emitter-Base Voltage	V _{EBO}	5		
Collector Current -Continuous	I _C	200	mA	
Collector Dissipation	P _C	200	mW	
Junction and Storage Temperature	T _j , T _{stg}	-55 to 150	°C	

Electrical Characteristics: @ TA = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit	
Collector-base breakdown voltage	V _{(BR)CBO}	Ι _C =10μΑ, Ι _E =0	60			
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40		V	
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μΑ, I _C =0	5			
Collector cut-off current	I _{CBO}	V_{CB} =60V, I_{E} =0		0.05		
Collector cut-off current	I _{CEO}	V _{CE} =40V, I _B =0		0.5	μA	
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		0.05		
DC current gain	h _{FE}	V_{CE} =1V, I_{C} =0.1mA V_{CE} =1V, I_{C} =1mA V_{CE} =1V, I_{C} =10mA V_{CE} =1V, I_{C} =50mA V_{CE} =1V, I_{C} =100mA	40 70 100 60 30	300		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA I _C =50mA, I _B =5mA		0.25 0.3	V	
Base-emitter saturation voltage	V _{BE(sat)}	I _C =10mA, I _B =1mA I _C =50mA, I _B =5mA	0.65	0.85 0.95	v	
Transition frequency	f _T	V _{CE} =20V, I _E = 10mA f=100MHz	300		MHz	

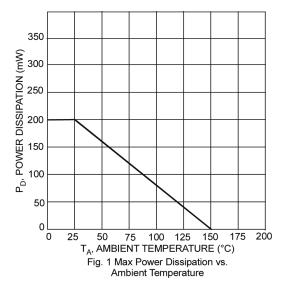


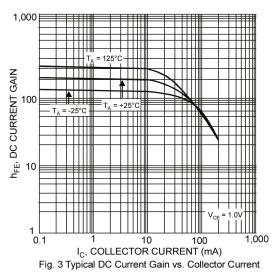
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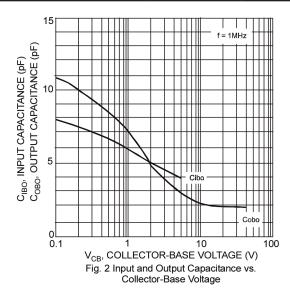


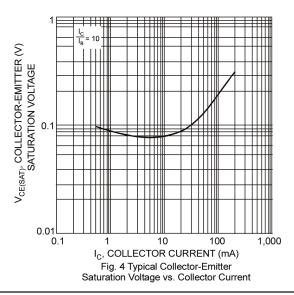
Electrical Characteristics: @ TA = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector output capacitance	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz		4	pF
Noise figure	NF	V_{CE} =5V, I_{C} =0.1mA, f=1KHz, R_{g} =1K Ω		5	dB
Delay time	t _d	V_{CC} =3V, V_{BE} =0.5V, I_{C} =10mA, I_{R} =1mA		35	
Rise time	t _r	I _C =10IIIA,I _B =1IIIA		35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA,		200	
Fall time	t _f	$V_{CC} = 3V, I_{C} = 10mA,$ $I_{B1} = I_{B2} = 1mA$		50	







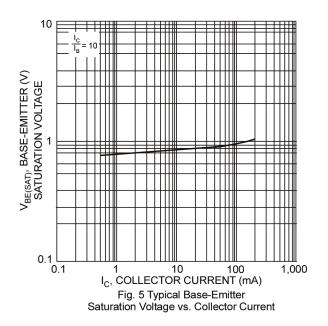


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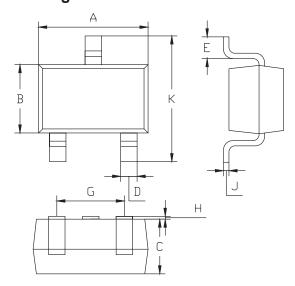


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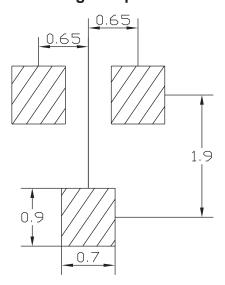


Package Outline:



SOT-323				
Dim.	Min.	Max.		
А	1.8	2.2		
В	1.15	1.35		
С	1 Typical			
D	0.15	0.35		
E	0.25	0.4		
G	1.2	1.4		
Н	0.02	0.1		
J	0.1 Typical			
К	K 2.1 2.3			

Soldering Footprint:



Dimensions: Millimetres

Part Number Table

Description	Part Number	
Transistor, Bipolar, NPN, 40V, 200mA	MMST3904-7-F	

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